2SB649(A)

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

WR0459I ṂṂ Ŀ SQS ᴂṀ ɥ s Ⅱ ㇕ Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

љ 5VG99<+D, Й ´

Complementary pair with 2SD669(A).

/ Applications

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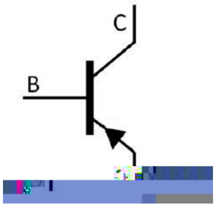
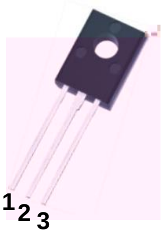
Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning

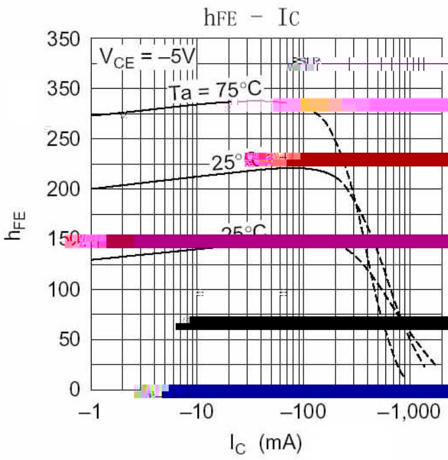


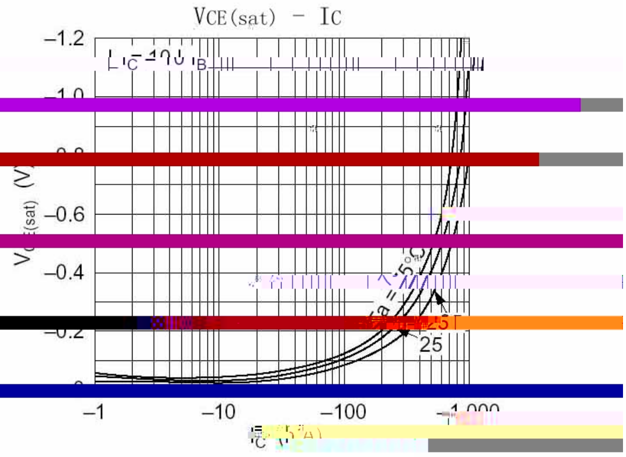
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

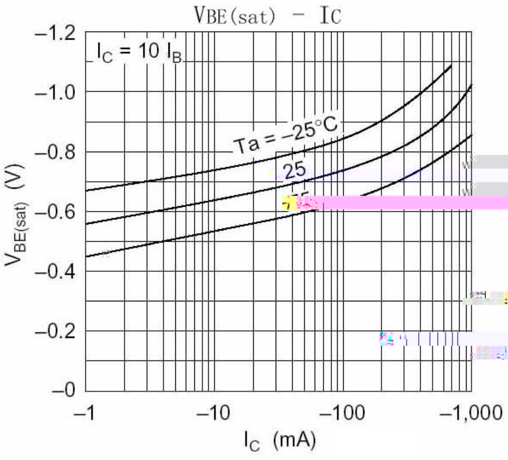
/ h_{FE} Classifications & Marking

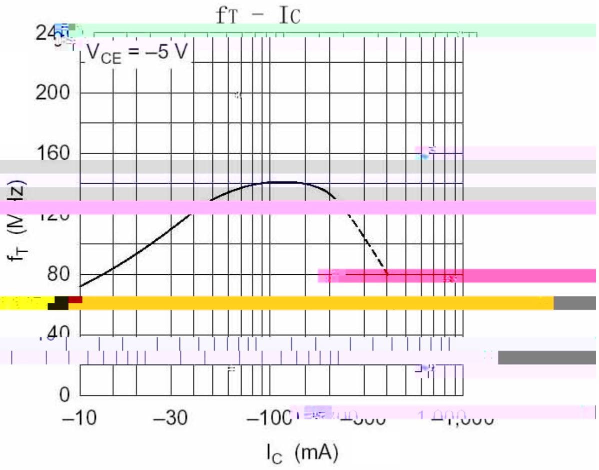
h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

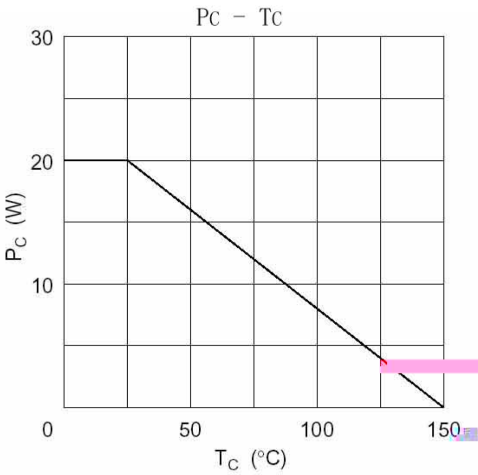
/ Electrical Characteristic Curve

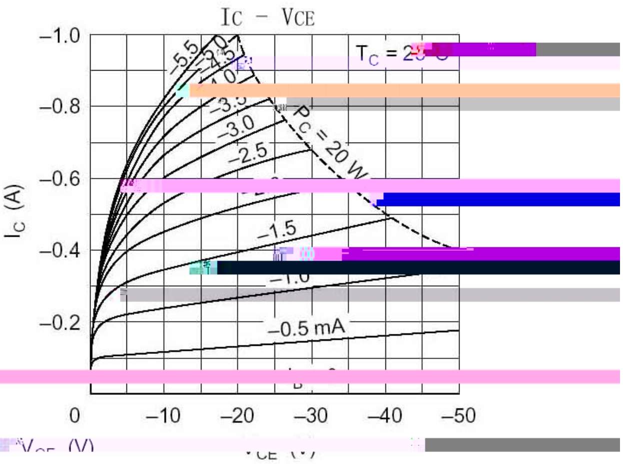

hFE − IC


VCE(sat) − IC


VBE(sat) − IC

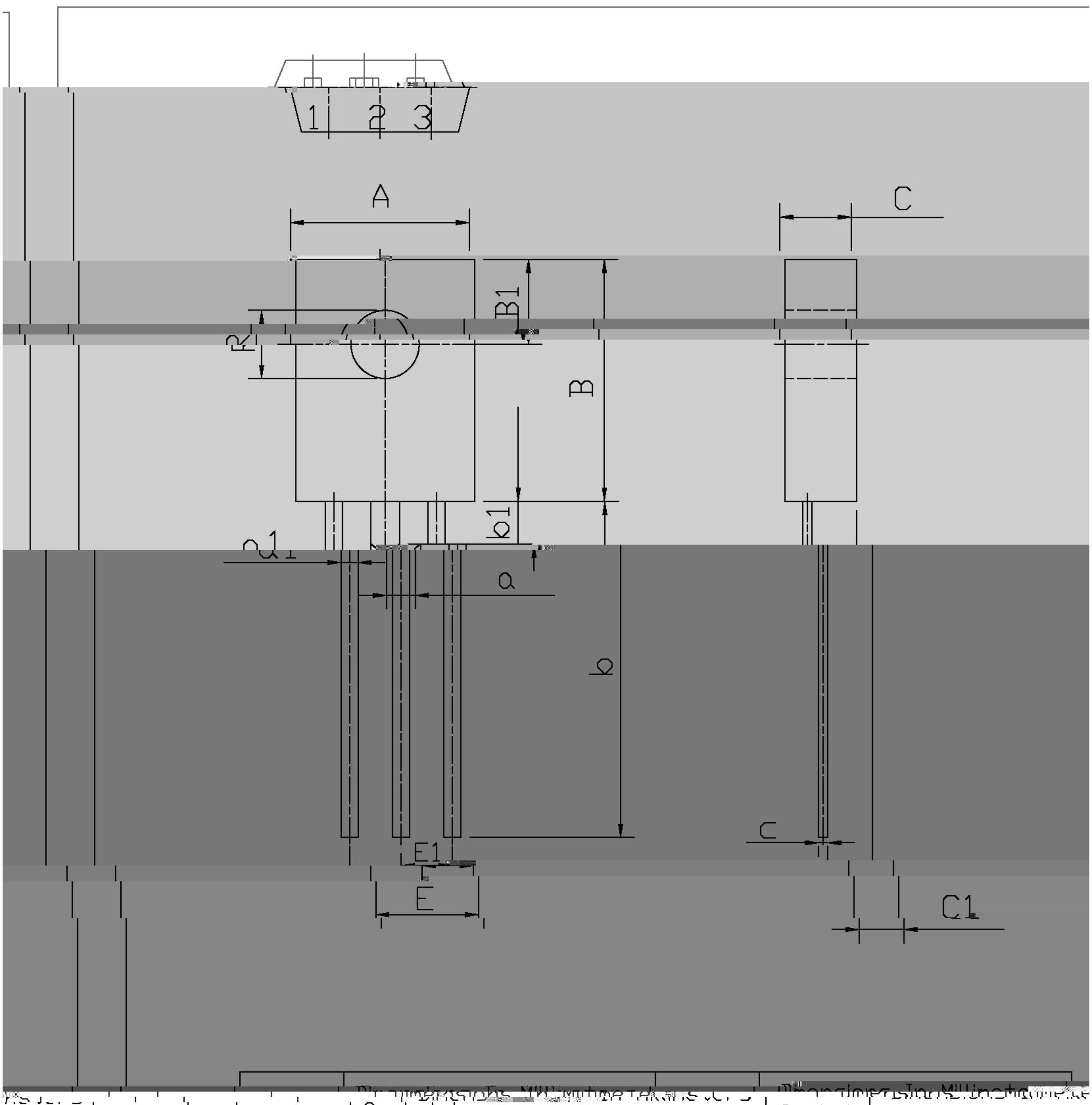

fT − IC


PC − TC


IC − VCE

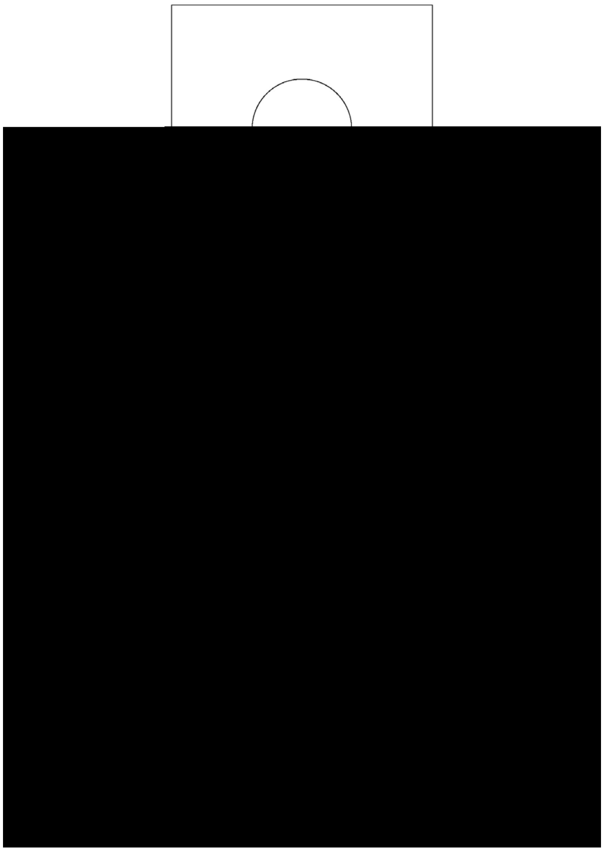
/ Package Dimensions

TO-126F 单位：mm



Symbol	Dimensions In Millimeters Min	Max	Symbol	Dimensions In Millimeters Min	Max
A	7.8	8.2	a1	0.66	0.86

/ Marking Instructions



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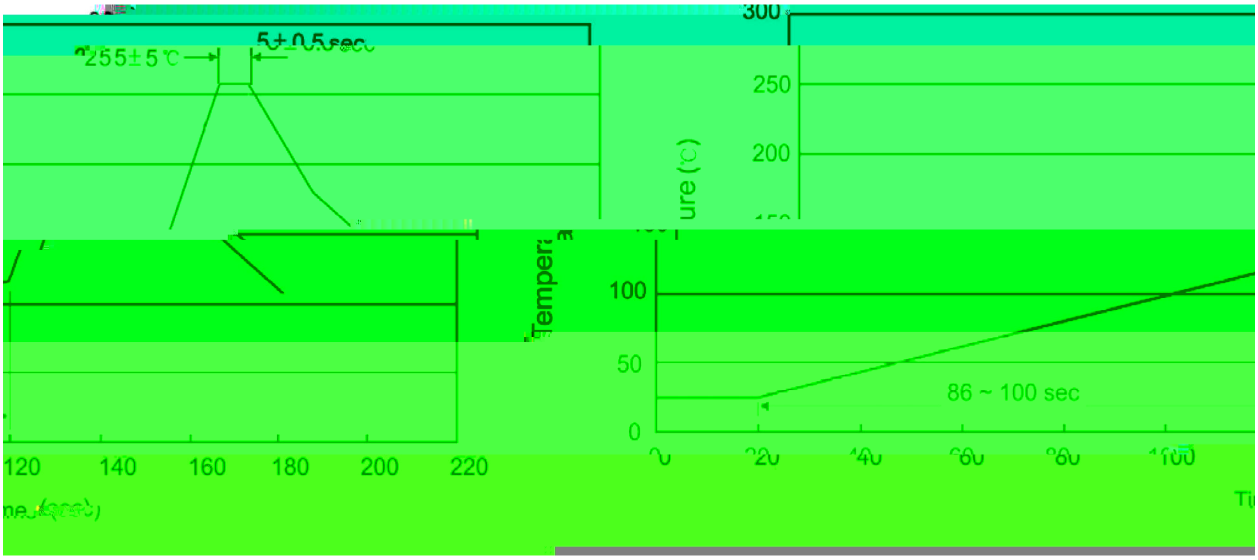
Note:

BR:	Company Code
B649 :	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ	Note:
1 ἱ ♬ □ ẙ 25 Ḱ 150 ɫ ı `H ڗ 60 Ḱ 90sec;	1.Preheating:25~150 ɫ , Time:60~90sec.
2 Ś Ӫ □ ẙ 255 ° 5 ɫ ı `H ڗ ʿY ﾊ ꭗ 5 ° 0.5sec;	2.Peak Temp.:255 ° 5 ɫ , Duration:5 ° 0.5sec.
3 ì ˙ Ỵ ˛ ɔ ه ẙ ꭗ 2 Ḱ 10 ɫ /sec.	3. Cooling Speed: 2~10 ɫ /sec.

5 • **Ủ 2** **ỗ** **ʙ** **I** 255 °